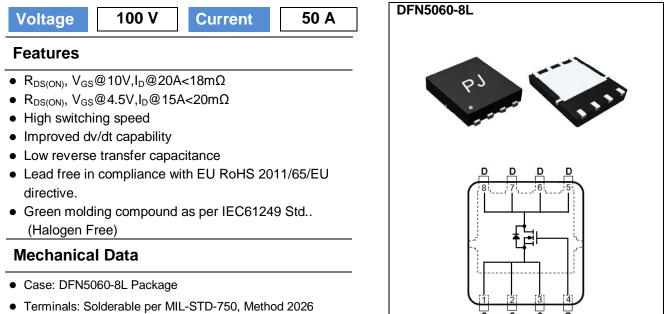
PAN	ĴΪΤ
	SEMI CONDUCTOR

### **100V N-Channel Enhancement Mode MOSFET**



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage Gate-Source Voltage		V <sub>DS</sub>	100	V	
		V <sub>GS</sub>	<u>+</u> 20	V	
Continuous Drain Current	T <sub>C</sub> =25°C		50		
	T <sub>C</sub> =100°C	ID	31	А	
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	150		
Power Dissipation	T <sub>c</sub> =25°C	6	83		
	T <sub>c</sub> =100°C	PD	33	W	
Continuous Drain Current	T <sub>A</sub> =25°C		7.5	A	
	T <sub>A</sub> =70°C	ID	6.0	A	
Power Dissipation	T <sub>A</sub> =25°C	5	2.0		
	T <sub>A</sub> =70°C	PD	1.3	W	
Single Pulse Avalanche Energy <sup>(Note 6)</sup>		E <sub>AS</sub>	156	mJ	
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C	
Typical Thermal Resistance <sup>(Note 4,5</sup>	5) Junction to Case	R <sub>θJC</sub>	1.5	0000	
	Junction to Ambient	R <sub>0JA</sub>	62.5	°C/W	

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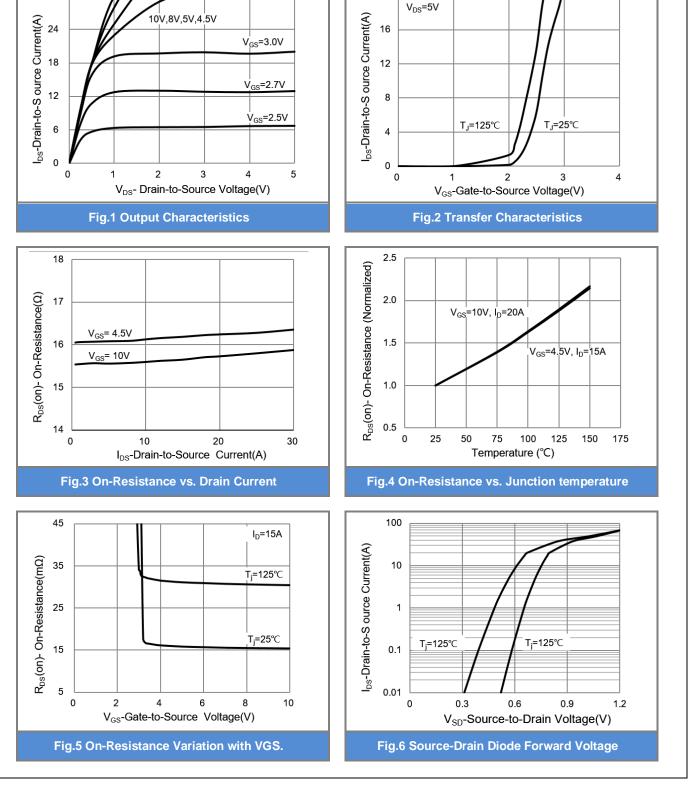


### **Electrical Characteristics** ( $T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	100	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250$ uA	1	1.6	2.5	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V,I <sub>D</sub> =20A	-	15.5	18	mΩ
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V,I <sub>D</sub> =15A	-	16	20	mΩ
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V,V <sub>GS</sub> =0V	-	-	1.0	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = <u>+</u> 20V,V <sub>DS</sub> =0V	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	$V_{DS}$ =50V, $I_{D}$ =30A, $V_{GS}$ =10V <sup>(Note 3)</sup>	-	95	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	11	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	18	-	
Input Capacitance	Ciss	· V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, · f=1.0MHZ	-	5173	-	
Output Capacitance	Coss		-	226	-	pF
Reverse Transfer Capacitance	Crss		-	66	-	
Turn-On Delay Time	td <sub>(on)</sub>	$V_{DD}$ =50V, $I_{D}$ =30A, $V_{GS}$ =10V, $R_{G}$ =3 $\Omega$ (Note 3)	-	29	-	
Turn-On Rise Time	tr		-	61	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	154	-	ns
Turn-Off Fall Time	t <sub>f</sub>		-	84	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>		-	-	50	А
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =20A,V <sub>GS</sub> =0V	-	0.8	1.3	V

NOTES :

- 1. Pulse width</br>
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited.
- 5.  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch<sup>2</sup> with 2oz.square pad of copper.
- 6. The test condition is L=0.5mH, I\_{AS}=25A, V\_{DD}=25V, V\_{GS}=10V, R\_G=25ohm, Starting T\_J=25^{o}C
- 7. Guaranteed by design, not subject to production testing.



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## TYPICAL CHARACTERISTIC CURVES

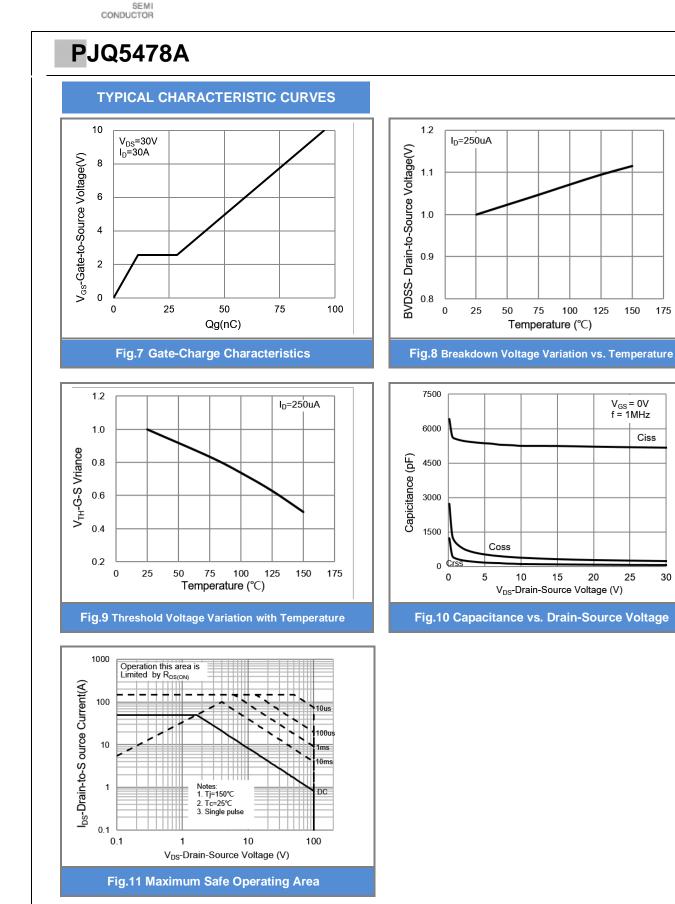
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**PJQ5478A** 





PANJ



175

125

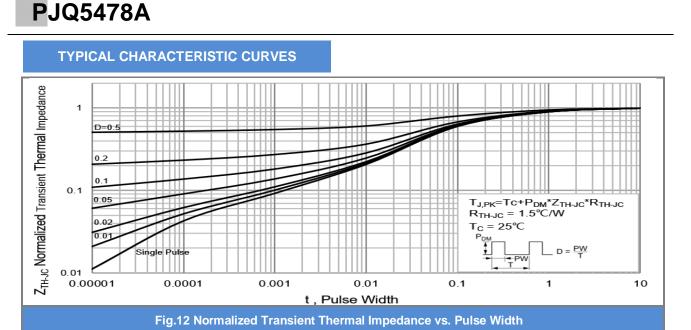
150

V<sub>GS</sub> = 0V f = 1MHz

25

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Ciss



## PANJIT SEMI CONDUCTOR





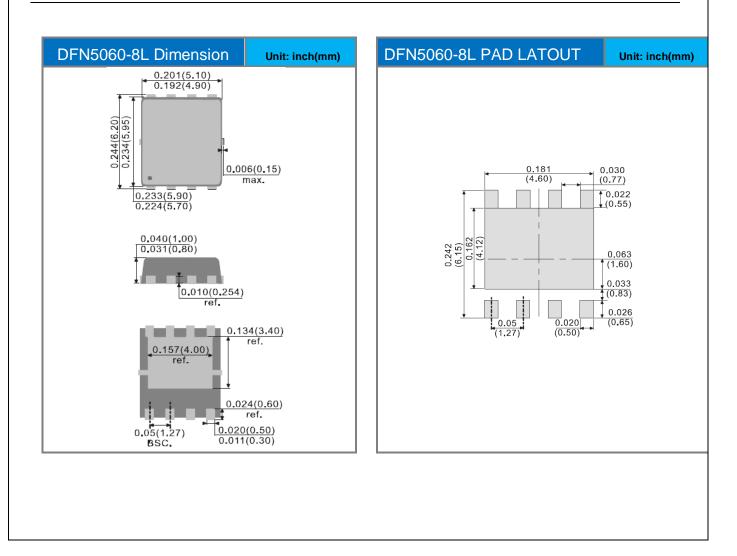




#### PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5478A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5478A	Halogen free

#### **Packaging Information & Mounting Pad Layout**





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